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ABSTRACT OF THE DISCLOSURE

The invention provides a method for predicting a process surface profile that a given plasma process will create on a process substrate. The prediction is based on a test surface profile, the experimental outcome of a test process which is in general different from the plasma process of interest. In another aspect, the invention provides a technique for defining a plasma process that will produce a desired surface profile. Thus, in related aspects, the invention also provides apparatus for predicting a process surface profile and determining process values, a method of configuring a plasma reactor, a method of making semiconductor devices requiring limited empirical calibration, and a device made according to the method.